

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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 APPLICANT
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GROUP

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
LP	5,640,343	06/17/97	Gallagher, et al.			
LP	6,081,445	06/27/00	Shi, et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

LP	Scheuerlein, et al., "A 10ns Read and Write Non-Volatile Memory Array Using A Magnetic Tunnel Junction and FET Switch in Each Cell" ISSCC Digest of Technical Papers, TA7.2, February 2000, pages 94-95, 128-129, 409-410
	Durlam, et al, "Nonvolatile RAM Based On Magnetic Tunnel Junction Elements, ISSCC Digest of Technical Papers, TA7.3, February 2000, pages 96-97, 130-131, 410-411
LP	Numata, et al., "Magnetic Random Access Memory(MRAM), Technical Report of IEICE, March 2000, pages 13-18
	Naji, et al., "A 256kb 3.0V 1TMTJ Nonvolatile Magnetoresistive RAM" ISSCC Digest of Technical Papers, TA7.6, February 6, 2001, pages 94-95, 122-123, 404-405, 438
LP	US Patent Application Serial No. 09/887,321, Filed June 25, 2001, Atty. Docket No. 57454-137
LP	US Patent Application Serial No. 09/834,638, Filed April 16, 2001, Atty. Docket No. 57454-075
LP	US Patent Application Serial No. 09/805,043, Filed March 14, 2001, Atty. Docket No. 57454-039
LP	US Patent Application Serial No. 09/832,025, Filed April 11, 2001, Atty. Docket No. 57454-070
LP	US Patent Application Serial No. 09/852,087, Filed May 10, 2001, Atty. Docket No. 57454-111
LP	US Patent Application Serial No. 09/944, 346, Filed September 4, 2001, Atty. Docket. No. 57454-189

EXAMINER

DATE CONSIDERED

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